TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

POWER GaAs MMIC TMD0507-2

Features:

■ HIGH POWER

■ BROAD BAND INTERNALLY MATCHED

P1dB=33 dBm at 5.1 to 7.2 GHz

■ HIGH GAIN

■ HERMETICALLY SEALED PACKAGE

G1dB=22 dB at 5.1 to 7.2 GHz

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	Vdd	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	W	0. 1
FLANGE TEMPERATURE	Tf	${\mathcal C}$	-30~+80
STORAGE TEMPERATURE	Tstg	${\mathcal C}$	$-65 \sim +175$

RF CHARACTERISTICS (Ta=25°C)

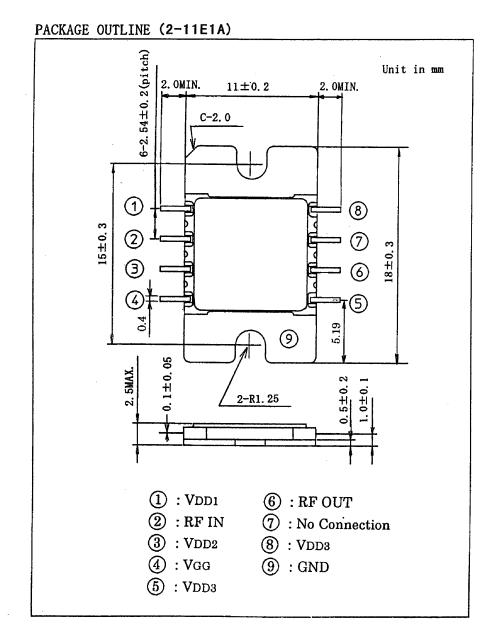
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CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB	P1dB	VDD1=VDD2=VDD3=	dBm	32.0	33. 0	
Gain Compression Point		10V,				
Power Gain at 1 dB	G1dB	VGG=-5 V	dB	20.0	22. 0	
Gain Compression Point		f= 5.1-7.2 GHz				
Drain Current	IDD *		A		1. 70	2.00
Input VSWR	VSWRi				_	3. 0

^{*} IDD=IDD1+IDD2+IDD3

[★] The information contained herein may be changed without prior notice. It is therefore advisable to contact TOSHIBA before proceeding with the design of equipment incorporating this product.



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HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260° C. Flanges of devices should be attached using screws and washers. Recommended torques are $0.18\text{-}0.20~\text{N}\cdot\text{m}$.